

MRF466

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

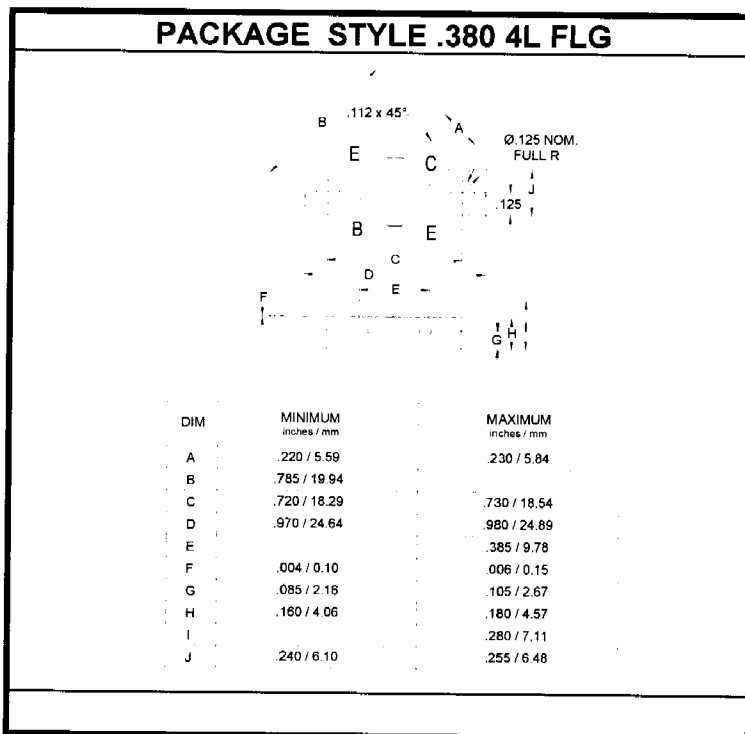
MRF466 is Designed for power amplifier applications from 2.0 to 30MHz.

FEATURES:

- $P_G = 15$ dB min. at 40 W/30 MHz
- $IMD_3 = -30$ dBc max. at 40 W (PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.0 A
V_{CBO}	65 V
V_{CEO}	35 V
P_{DISS}	175 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	1.0 $^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	35			V
BV_{CES}	$I_C = 100$ mA	65			V
BV_{EBO}	$I_E = 1.0$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 0.5$ A	10		80	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz		125	200	pF
G_{PE}	$V_{CE} = 28$ V $I_{CQ} = 20$ mA $f = 30$ MHz	15	19		dB
η	$P_{OUT} = 40$ W (PEP)	40			%
IMD_3			-40	-30	dBc

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